_				
S	ΗĿ	Ŀ١	1	OF

_		+ 2/6/4	SHEET 1 O
FORMATION DISCLOSURE STATEMENT	ATTY, DOCKET NO. MICRON.214DDV1	APPLICATION NO. 10/648,103	
BADEN (USE SEVERAL SHEETS IF NECESSARY)	APPLICANT Liu, et al.		<del>,</del>
TRADEM (USE SEVERAL SHEETS IF NECESSARY)	FILING DATE August 22, 2003	GROUP Unknown	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MDP	6028786		Nishimura			
	6136705		Blair			
	6153443		Durlam, et al.			
	6174737		Durlam, et al.			
	6,218,302		Braeckelmann, et al.			
1	6338899		Fukuzawa, et al.			
	6358756		Sandhu, et al.			
	6379978		Goebel, et al.			
	6391658		Gates, et al.			
1	2002 / 0041514 A1	1	Scheler			
LIN	6,440,753		Ning, et al			

		FORE	GN PATENT DOCUMENTS				
EXAMINER	DOCUMENT NUMBER	DATE COUNTRY	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
INITIAL						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

L:\DOCS\MSO\MSO-5307.DOC 013004

EXAMINER MALES THE STATE OF	DATE CONSIDERED	12/8	14	
*EXAMINER INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM	ON IS IN CONFORMANCE WI	TH MPEP 60 ON TO APPL	9, DR	AW LINE THROUGH CITATION IF NOT

_		
`		
•		
,		
,		

COPY

	)
() H 8/22/3	ク

SHEET 1 OF 2

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. MICRON.2148V1 21400V1 APPLICATION NO. 10/037,182

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

APPLICANT Liu et al.

(USE SEVERAL SHEETS IF NECESSARY)

FILING DATE January 24, 2002 Herewith

GROUP Unknown

			U.S. PATENT DOCUMENTS	·		
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MOP	3,623,032	11/23/71	Schapira		•	
7	3,623,035	11/23/71	Kobayashi et al.			
	3,816,909	6/18/74	Maeda et al.			
	3,947,831	3/30/76	Kobayashi et al.			
	4,044,330	8/23/77	Johnson et al.			
	4,060,794	11/29/77	Feldman et al.			
	4,158,891	6/19/79	Fisher			
	4,455,626	6/19/84	Lutes			
	4,731,757	3/15/88	Daughton et al.			
	4,780,848	10/25/88	Daughton et al.			
	4,801,883	01/31/89	Muller et al.			<del></del>
	4,849,695	07/18/89	Muller et al.			
	4,945,397	07/31/90	Schuetz	<u> </u>		
	5,039,655	8/13/91	Pisharody ·			<del></del>
	5,064,499	11/12/91	Fryer			
	5,140,549	8/18/92	Fryer			· <del></del>
	5,496,759	3/5/96	Yue et al.			
	5,547,599	8/20/96	Wolfrey et al.			
	5,569,617	10/29/98	Yeh et al.		-	
	5,587,943	12/24/98	Torok et al.	<del> </del>		
	5,650,958	7/22/97	Gallagher et al.			
	5,701,222	12/23/97 .	Gill et al.			
	5,726,498	03/10/98	Licata et al.	<u> </u>		
<del>- </del>	5,741,435	4/21/98	Beetz, Jr. et al.			
1,	5,756,368	3/26/98	Berg et al.	-		
TIME	5,795,823	08/18/98	Avanzino et al.	<del>                                     </del>		

EXAMINER MALE DATE CONSIDERED 12/

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 809; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY, DOCKET NO. MICRON.249041 214 PDU) APPLICATION NO. <del>-10/057,1</del>82 Un known

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

APPLICANT Liu et al.

(USE SEVERAL SHEETS IF NECESSARY)

FILING DATE January 24, 2002 Herewith

**GROUP** Unknown

	U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
MOP	5,861,328	1/99	Tehrani et al.			•	
1	5,926,394	07/20/99	Nguyen et al.			09/30/96	
	5,956,267	9/21/99	Hurst et al.				
	5,982,658	11/09/99	Berg et al.				
MA	6,048,739	4/11/00	Hurst et al.				

FOREIGN PATENT DOCUMENTS							
EXAMINER	DOCUMENT NUMBER	NER DOCUMENT NUMBER DATE COUNTRY	CLASS	SUBCLASS	TRANSLATION		
INITIAL .					YES	МО	
MAR	DE 198 36 567 A 1	2/24/00	Germany				
1.	WO 00/19440	4/6/00	PCT				
	EP 0 776 011 A2	5/28/97	EPO .				
$\downarrow$	WO 98/20496	5/14/98	EPO				
MAY	2000-30222	1/2000	Japan				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
MDP	Honeywell Brochure entitled Pohm et al., "The Architecture of a High Performance Mass Store with GMR Memory Cells," Nonvolatile Electronics, pp. 1-3.
	Pohm et al., "Experimental and Analytical Properties of 0.2 Micron Wide, Multi-Layer, GMR, Memory Elements," IEEE Transactions on Magnetics, Vol. 32, No. 5, September 1996, pp. 4645-4647.
	Prinz, Gary, "Magnetoelectronics," Science, Vol. 282, November 27, 1998, pp. 1660-1663.
J	Wang, Zhi G. et al., "Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory," <u>IEEE Transactions on Magnetics</u> , Vol. 33, No. 6, November 1997, pp.4498-4512.
MSP	Razavi et al., * Design Techniques for High-Speed, High-Resolution Comparators*, IEEE Journal of Solid State Circuit, Vol. 27, No. 12, December 1992

W:\DOCS\JPF\JPF-1091.DOC 021902

EXAMINE

DATE CONSIDERED

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 6/99; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.